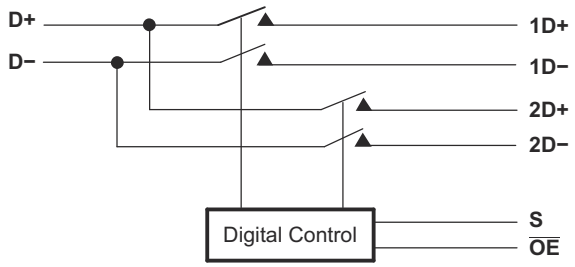
TS3USB221E High-Speed USB 2.0 (480Mbps) 1:2 Multiplexer – Demultiplexer Switch With Single Enable and IEC Level 3 ESD Protection

1 Features

- V_{CC} operation of 2.3V to 3.6V
- Switch I/OS accept signals up to 5.5V
- 1.8V compatible control-pin inputs
- Low-power mode when $\overline{OE}$ is disabled (1µA)
- r_{ON} = 6Ω maximum
- Δr_{ON} = 0.2Ω typical
- $C_{IO(ON)}$ = 7pf maximum
- Low power consumption (30µA maximum)
- ESD performance tested:
  - 7000V human body model per JEDEC JS-001
  - 1000V charged-device model per JEDEC JS-002
- ESD performance I/O port to GND:
  - 12kV human body model (JEDEC JS-001)
  - ±7kV contact discharge (IEC 61000-4-2)
- High bandwidth (1GHz typical)

2 Applications

- Routes signals for USB 1.0, 1.1, and 2.0
- Mobile phones
- Digital cameras
- Notebooks
- USB I/O expansion
- MHL 1.0



Block Diagram

3 Description

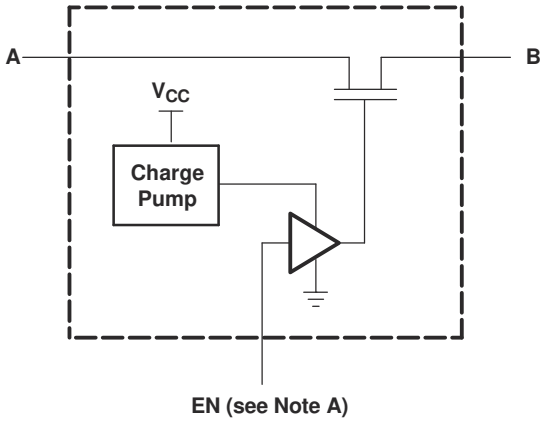
The TS3USB221E is a high-bandwidth switch specially designed for the switching of high-speed USB 2.0 signals in handset and consumer applications, such as cell phones, digital cameras, and notebooks with hubs or controllers with limited USB I/Os. The wide bandwidth (1GHz) of this switch allows signals to pass with minimum edge and phase distortion. The device multiplexes differential outputs from a USB host device to one of two corresponding outputs. The switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. The TS3USB221E is designed for low bit-to-bit skew and high channel-to-channel noise isolation, and is compatible with various standards, such as high-speed USB 2.0 (480Mbps).

The TS3USB221E integrates ESD protection cells on all pins, is available in a SON package (3mm × 3mm) as well as in a tiny µQFN package (2mm × 1.5mm) and is characterized over the free-air temperature range from –40°C to 85°C.

Package Information

PART NUMBER	PACKAGE(1)	PACKAGE SIZE(2)
TS3USB221E	DRC (VSON, 10)	3mm × 3mm
	RSE (UQFN, 10)	2mm × 1.5mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.
(2) The package size (length × width) is a nominal value and includes pins, where applicable.



A. EN is the internal enable signal applied to the switch.

Simplified Schematic, Each FET Switch (SW)

Table of Contents

4 Pin Configuration and Functions

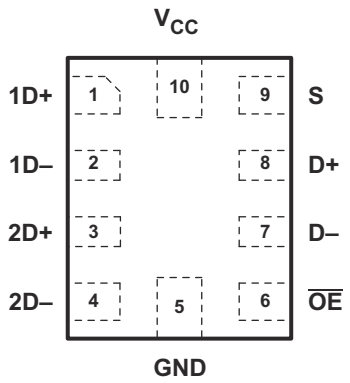


Figure 4-1. RSE Package, 10-Pin UQFN (Top View)

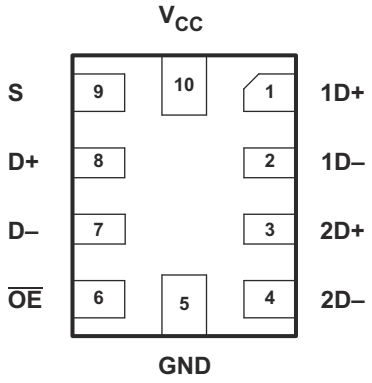


Figure 4-2. RSE Package, 10-Pin UQFN (Bottom View)

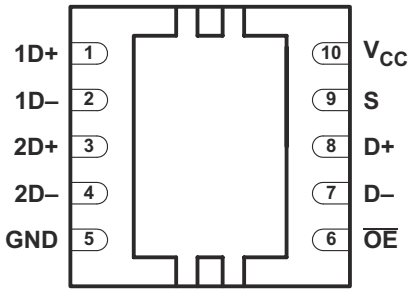


Figure 4-3. DRC Package, 10-Pin VSON (Top View)

Table 4-1. Pin Functions

PIN		TYPE[1]	DESCRIPTION
NAME	NO.		
1D+	1	I/O	USB port 1
1D–	2	I/O	
2D+	3	I/O	USB port 2
2D–	4	I/O	
GND	5	—	Ground
$\overline{OE}$	6	I	Bus-switch enable
D–	7	I/O	Common USB port
D+	8	I/O	
S	9	I	Select input
V_{CC}	10	—	Supply voltage

(1) I = input, O = output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	4.6	V
V_{IN}	Control input voltage(2) (2) (3)		–0.5	7	V
$V_{I/O}$	Switch I/O voltage(2) (3) (4)		–0.5	7	V
I_{IK}	Control input clamp current	V_{IN} < 0		–50	mA
$I_{I/OK}$	I/O port clamp current	$V_{I/O}$ < 0		–50	mA
$I_{I/O}$	ON-state switch current(5)			±120	mA
	Continuous current through V_{CC} or GND			±100	mA
θ_{JA}	Package thermal impedance(6)	DRC package		48.7	°C/W
		RSE package		243	
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to ground, unless otherwise specified.
(3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(4) V_I and V_O are used to denote specific conditions for $V_{I/O}$.
(5) I_I and I_O are used to denote specific conditions for $I_{I/O}$.
(6) The package thermal impedance is calculated in accordance with JESD 51-7.

5.2 ESD Ratings

				VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	I/O pins to GND	±12000	V
			Pins GND, $\overline{OE}$, S and V_{CC}	±7000	
		Contact discharge (IEC 61000-4-2)	I/O pins to GND	±7000	
		Charged-device model (CDM), per JEDEC specification JESD-002(2)		±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

See (1).

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level control input voltages	V_{CC} = 2.3 V to 2.7 V	0.46 × V_{CC}		V
		V_{CC} = 2.7 V to 3.6 V	0.46 × V_{CC}		
V_{IL}	Low-level control input voltage	V_{CC} = 2.3 V to 2.7 V		0.25 × V_{CC}	V
		V_{CC} = 2.7 V to 3.6 V		0.25 × V_{CC}	
$V_{I/O}$	Data input/output voltage(2)		0	5.5	V
T_A	Operating free-air temperature		–40	85	°C

(1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the *Implications of Slow or Floating CMOS Inputs* application note.
(2) The I/O pins are 5.5V tolerant and functional for the entire range. However, for VI/O >3.6V, channel R_{ON} will be high. Use 3.3V power supply for best results.

5.4 Thermal Information

THERMAL METRIC[1]		TS3USB221E		UNIT
		DRC (VSON)	RSE (UQFN)	
		10 PINS	10 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	57.7	204.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	87.7	118.1	
$R_{\theta JB}$	Junction-to-board thermal resistance	32.6	121.5	
ψ_{JT}	Junction-to-top characterization parameter	8.2	13.9	
ψ_{JB}	Junction-to-board characterization parameter	32.8	121.2	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	18.5	N/A	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application note.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)[1]

PARAMETER		TEST CONDITIONS			MIN	TYP[2]	MAX	UNIT
V_{IK}		V_{CC} = 3.6 V, 2.7 V,	I_I = –18 mA		–1.8			V
I_{IN}	Control inputs	V_{CC} = 3.6 V, 2.7 V, 0 V,	V_{IN} = 0 V to 3.6 V				±1	µA
I_{OZ} [3]		V_{CC} = 3.6 V, 2.7 V, V_O = 0 V to 5.25 V, V_I = 0 V,	V_{IN} = V_{CC} or GND, Switch OFF				±1	µA
I_{OFF}		V_{CC} = 0 V	$V_{I/O}$ = 0 V to 5.25 V				±2	µA
			$V_{I/O}$ = 0 V to 3.6 V				±2	
			$V_{I/O}$ = 0 V to 2.7 V				±1	
I_{CC}		V_{CC} = 3.6 V, 2.7 V, V_{IN} = V_{CC} or GND,	$I_{I/O}$ = 0 V, Switch ON or OFF				30	µA
I_{CC} (low power mode)		V_{CC} = 3.6 V, 2.7 V, V_{IN} = V_{CC} or GND	Switch disabled ($\overline{OE}$ in high state)				1	µA
I_{CC} [4]	Control inputs	One input at 1.8 V, Other inputs at V_{CC} or GND	V_{CC} = 3.6 V				20	µA
			V_{CC} = 2.7 V				0.5	
C_{in}	Control inputs	V_{CC} = 3.3 V, 2.5 V,	V_{IN} = 3.3 V or 0 V			1.5	2.5	pF
$C_{io(OFF)}$		V_{CC} = 3.3 V, 2.5 V,	$V_{I/O}$ = 3.3 V or 0 V,	Switch OFF		3.5	5	pF
$C_{io(ON)}$		V_{CC} = 3.3 V, 2.5 V,	$V_{I/O}$ = 3.3 V or 0 V,	Switch ON		6	7.5	pF
r_{ON} [5]		V_{CC} = 3 V, 2.3 V	V_I = 0 V,	I_O = 30 mA		3	6	Ω
			V_I = 2.4 V,	I_O = –15 mA		3.4	6	
Δr_{ON}		V_{CC} = 3 V, 2.3 V	V_I = 0 V,	I_O = 30 mA		0.2		Ω
			V_I = 1.7,	I_O = –15 mA		0.2		
$r_{ON(flat)}$		V_{CC} = 3 V, 2.3 V	V_I = 0 V,	I_O = 30 mA		1		Ω
			V_I = 1.7,	I_O = –15 mA		1		

(1) V_{IN} and I_{IN} refer to control inputs. V_I, V_O, I_I, and I_O refer to data pins.
(2) All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
(3) For I/O ports, the parameter I_{OZ} includes the input leakage current.
(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.
(5) Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

5.6 Dynamic Electrical Characteristics, V_{CC} = 3.3 V ±10%

over operating range, T_A = –40°C to 85°C, V_{CC} = 3.3 V ±10%, GND = 0 V

PARAMETER		TEST CONDITIONS	TYP(1)	UNIT
X_{TALK}	Crosstalk	R_L = 50 , f = 250 MHz	–40	dB
O_{IRR}	OFF isolation	R_L = 50 , f = 250 MHz	–40	dB
BW	Bandwidth (–3 dB)	R_L = 50	1	GHz

(1) For Maximum or Minimum conditions, use the appropriate value specified under *Electrical Characteristics* for the applicable device type.

5.7 Dynamic Electrical Characteristics, V_{CC} = 2.5 V ±10%

over operating range, T_A = –40°C to 85°C, V_{CC} = 2.5 V ±10%, GND = 0 V

PARAMETER		TEST CONDITIONS	TYP(1)	UNIT
X_{TALK}	Crosstalk	R_L = 50 , f = 250 MHz	-39	dB
O_{IRR}	OFF isolation	R_L = 50 , f = 250 MHz	-40	dB
BW	Bandwidth (3 dB)	R_L = 50	1	GHz

(1) For Maximum or Minimum conditions, use the appropriate value specified under *Electrical Characteristics* for the applicable device type.

5.8 Switching Characteristics, V_{CC} = 3.3 V ±10%

over operating range, T_A = –40°C to 85°C, V_{CC} = 3.3 V ±10%, GND = 0 V

PARAMETER			MIN	TYP(1)	MAX	UNIT
t_{pd}	Propagation delay(2) (3)			0.25		ns
t_{ON}	Line enable time	S to D, nD			30	ns
		$\overline{OE}$ to D, nD			17	
t_{OFF}	Line disable time	S to D, nD			12	ns
		$\overline{OE}$ to D, nD			10	
$t_{SK(O)}$	Output skew between center port to any other port(2)			0.1	0.2	ns
$t_{SK(P)}$	Skew between opposite transitions of the same output (t_{PHL}– t_{PLH})(2)			0.1	0.2	ns

(1) For Maximum or Minimum conditions, use the appropriate value specified under *Electrical Characteristics* for the applicable device type.
(2) Specified by design
(3) The bus switch contributes no propagation delay other than the RC delay of the on resistance of the switch and the load capacitance. The time constant for the switch alone is of the order of 0.25 ns for 10-pF load. Because this time constant is much smaller than the rise/fall times of typical driving signals, it adds very little propagation delay to the system. Propagation delay of the bus switch, when used in a system, is determined by the driving circuit on the driving side of the switch and its interactions with the load on the driven side.

5.9 Switching Characteristics, V_{CC} = 2.5 V ±10%

over operating range, T_A = –40°C to 85°C, V_{CC} = 2.5 V ±10%, GND = 0 V

PARAMETER			MIN	TYP(1)	MAX	UNIT
t_{pd}	Propagation delay(2) (3)			0.25		ns
t_{ON}	Line enable time	S to D, nD			50	ns
		$\overline{OE}$ to D, nD			32	
t_{OFF}	Line disable time	S to D, nD			23	ns
		$\overline{OE}$ to D, nD			12	
$t_{SK(O)}$	Output skew between center port to any other port(2)			0.1	0.2	ns
$t_{SK(P)}$	Skew between opposite transitions of the same output (t_{PHL}– t_{PLH})(2)			0.1	0.2	ns

(1) For Maximum or Minimum conditions, use the appropriate value specified under *Electrical Characteristics* for the applicable device type.
(2) Specified by design

(3) The bus switch contributes no propagation delay other than the RC delay of the on resistance of the switch and the load capacitance. The time constant for the switch alone is of the order of 0.25 ns for 10-pF load. This time constant is much smaller than the rise/fall times of typical driving signals, therefore the time adds very little propagation delay to the system. Propagation delay of the bus switch, when used in a system, is determined by the driving circuit on the driving side of the switch and its interactions with the load on the driven side.

5.10 Typical Characteristics

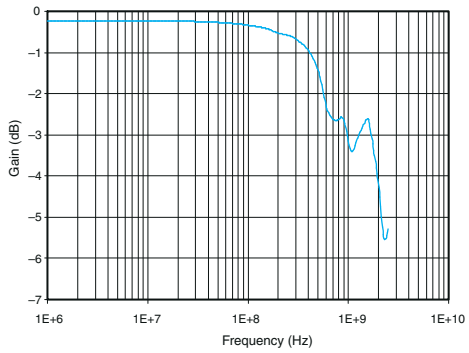


Figure 5-1. Gain vs Frequency

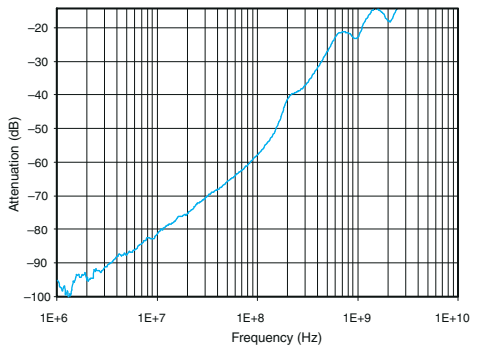


Figure 5-2. OFF Isolation vs Frequency

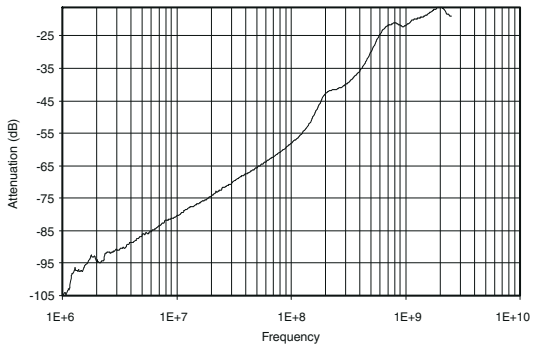


Figure 5-3. Crosstalk vs Frequency

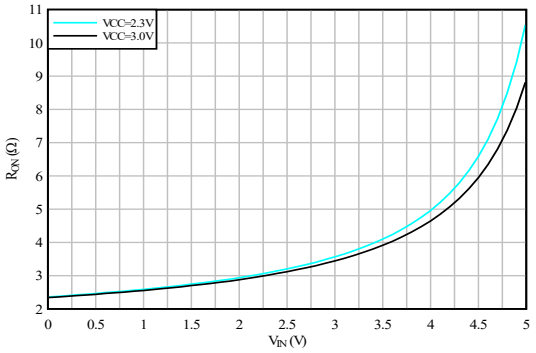
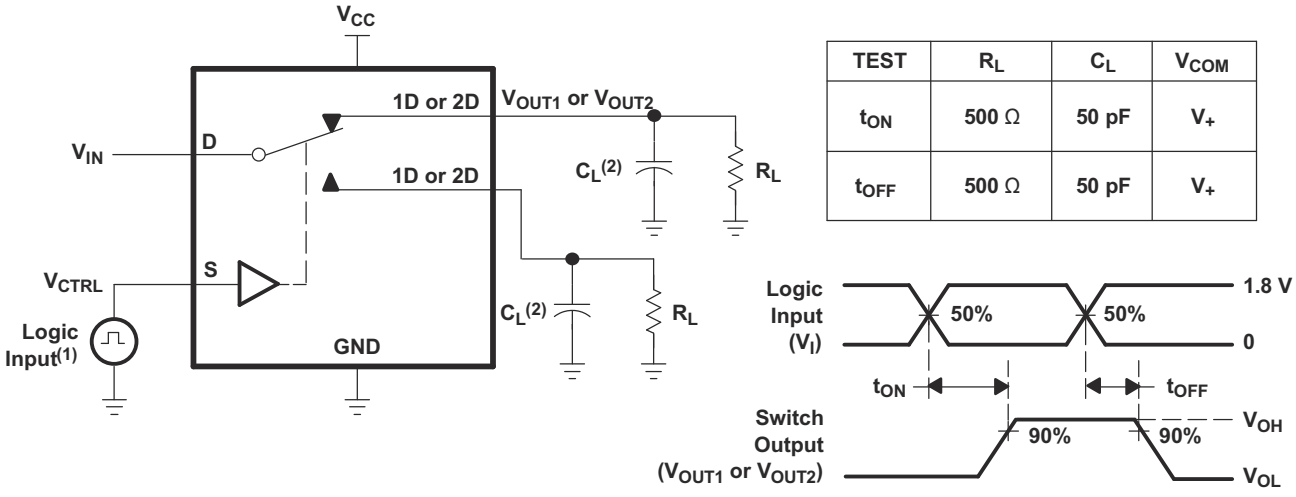


Figure 5-4. R_{on} vs V_{IN} (I_{OUT} = –30 mA)

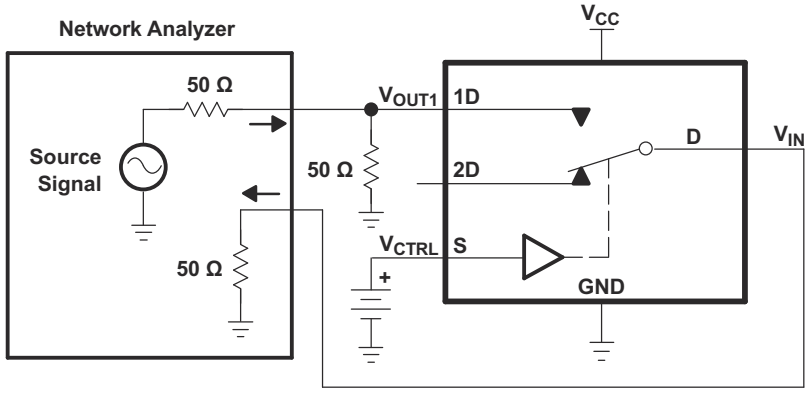
Parameter Measurement Information



TEST	R_L	C_L	V_{COM}
t_{ON}	500 Ω	50 pF	V_+
t_{OFF}	500 Ω	50 pF	V_+

(1) All input pulses are supplied by generators having the following characteristics: PRR≤ 10 MHz, Z_O = 50W, t_r < 5 ns, t_f < 5 ns.
(2) C_L includes probe and jig capacitance.

Figure 6-1. Turnon (T_{ON}) and Turnoff Time (T_{OFF})

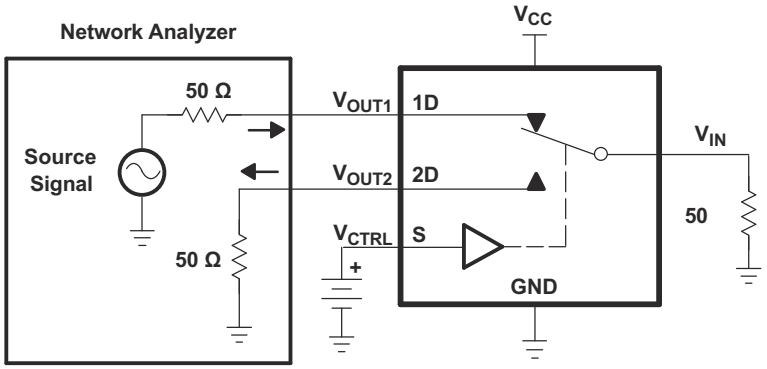


Channel OFF: 1D to D
V_{CTRL} = V_{CC} or GND

Network Analyzer Setup

Source Power = 0 dBm (632-mV P-P at 50-Ω load)
DC Bias = 350 mV

Figure 6-2. OFF Isolation (O_{ISO})



Channel ON: 1D to D
Channel OFF: 2D to D
V_{CTRL} = V_{CC} or GND

Network Analyzer Setup

Source Power = 0 dBm (632-mV P-P at 50-Ω load)
DC Bias = 350 mV

Figure 6-3. Crosstalk (X_{TALK})

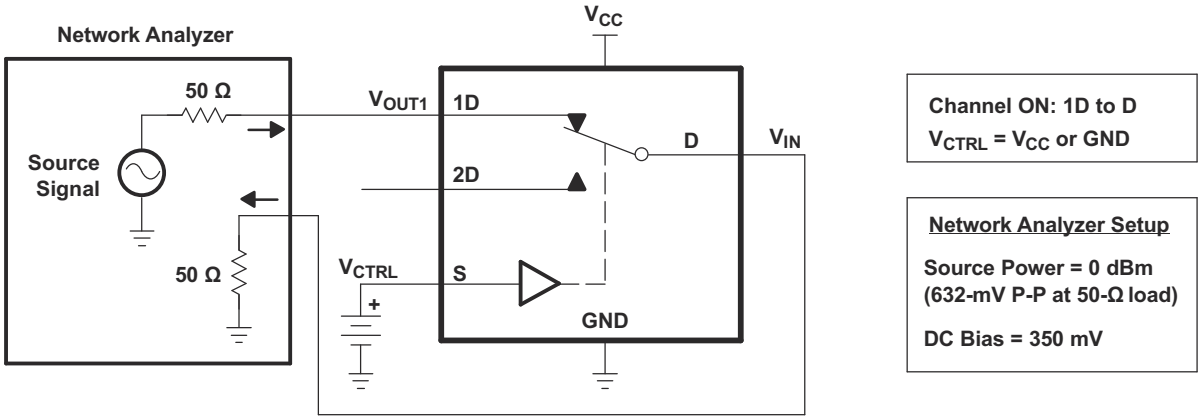


Figure 6-4. Bandwidth (BW)

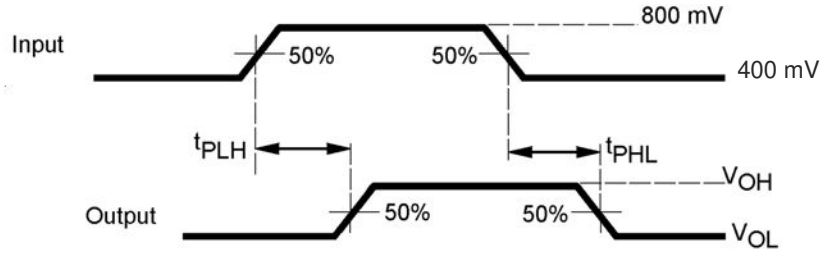


Figure 6-5. Propagation Delay

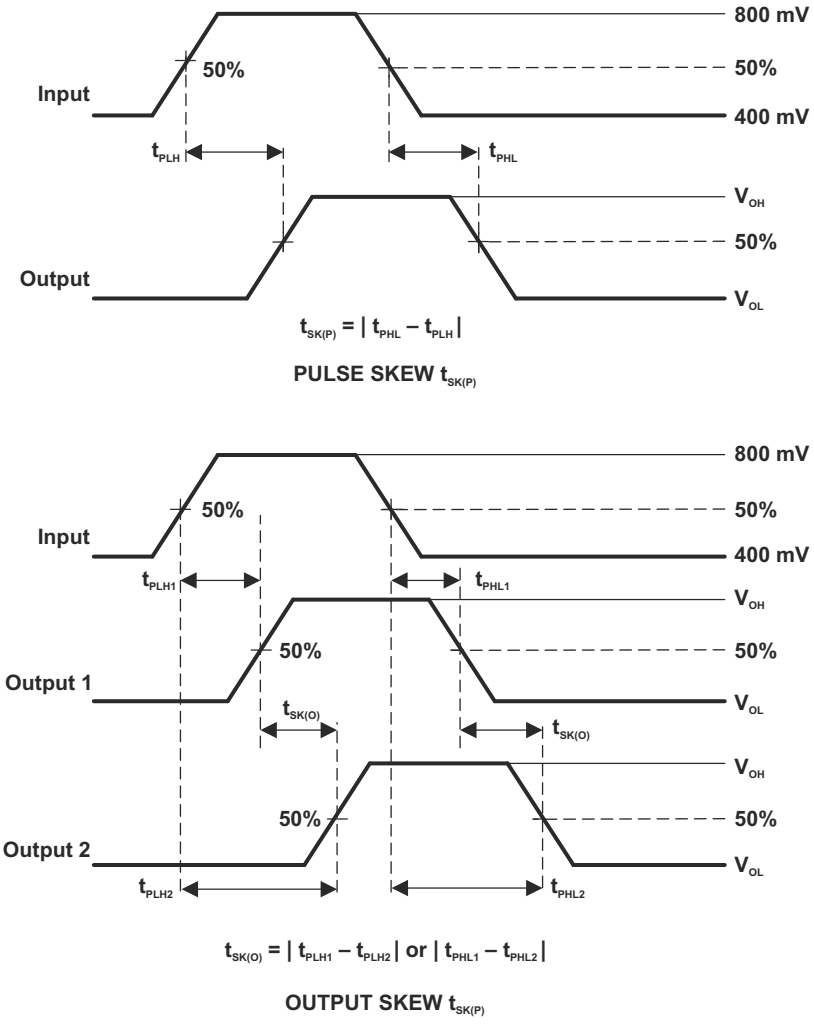


Figure 6-6. Skew Test

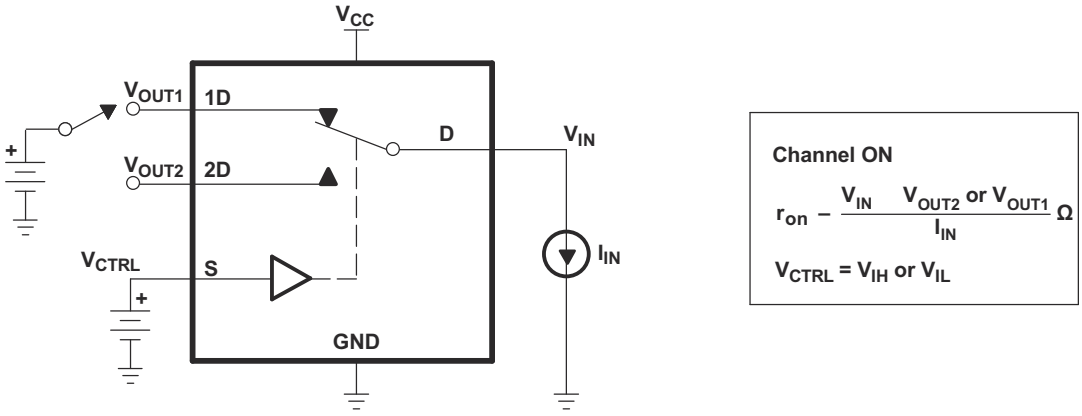
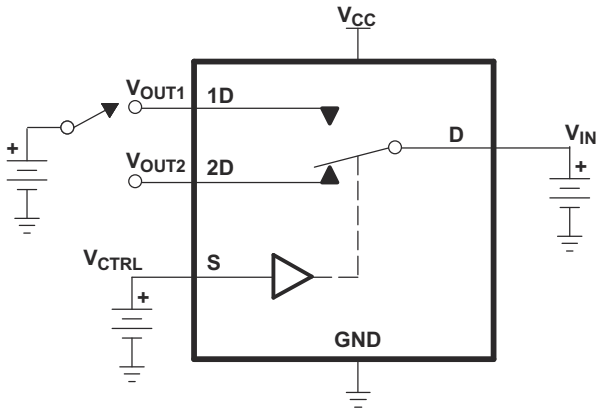
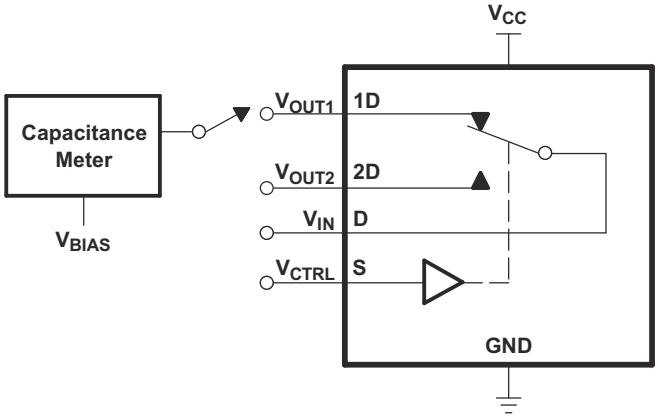


Figure 6-7. ON-State Resistance (R_{on})



OFF-State Leakage Current
Channel OFF
V_{CTRL} = V_{IH} or V_{IL}

Figure 6-8. OFF-State Leakage Current



V_{BIAS} = V_{CC} or GND
V_{CTRL} = V_{CC} or GND
Capacitance is measured at 1D, 2D, D, and S inputs during ON and OFF conditions.

Figure 6-9. Capacitance

6 Detailed Description

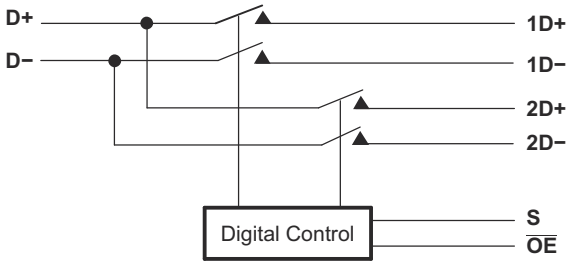
6.1 Overview

The TS3USB221E device is a 2-channel SPDT switch specially designed for the switching of high-speed USB 2.0 signals in handset and consumer applications, such as cell phones, digital cameras, and notebooks with hubs or controllers with limited USB I/Os. The wide bandwidth (1 GHz) of this switch allows signals to pass with minimum edge and phase distortion. The device multiplexes differential outputs from a USB host device to one of two corresponding outputs. The switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. The device also has a low power mode that reduces the power consumption to 1 µA for portable applications with a battery or limited power budget.

The device is designed for low bit-to-bit skew and high channel-to-channel noise isolation, and is compatible with various standards, such as high-speed USB 2.0 (480 Mbps).

The TS3USB221E device integrates ESD protection cells on all pins, is available in a SON package (3mm × 3mm) as well as in a tiny µQFN package (2mm × 1.5mm) and is characterized over the free-air temperature range from –40°C to 85°C.

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Low Power Mode

The TS3USB221E has a low power mode that reduces the power consumption to 1 µA when the device is not in use. To put the device in low power mode and disable the switch, the bus-switch enable pin $\overline{OE}$ must be supplied with a logic high signal.

6.4 Device Functional Modes

Table 6-1. Truth Table

S	$\overline{OE}$	FUNCTION
X	H	Disconnect
L	L	D = 1D
H	L	D = 2D

7 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

There are many USB applications in which the USB hubs or controllers have a limited number of USB I/Os. The TS3USB221E can effectively expand the limited USB I/Os by switching between multiple USB buses to interface them to a single USB hub or controller. The TS3USB221E can also be used to connect a single controller to two USB connectors.

7.2 Typical Application

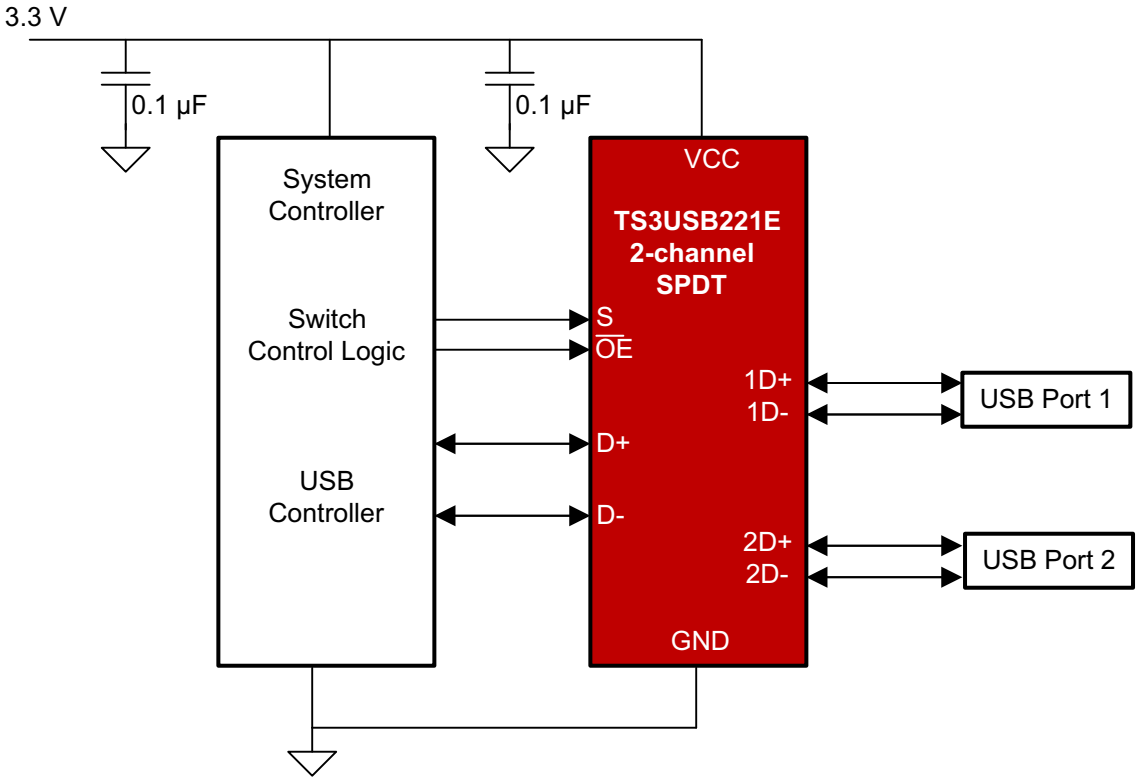


Figure 7-1. Simplified Schematic

7.2.1 Design Requirements

Follow the design requirements of the USB 1.0, 1.1, and 2.0 standards.

TI recommends that the digital control pins S and $\overline{OE}$ be pulled up to V_{CC} or down to GND to avoid undesired switch positions that could result from the floating pin.

7.2.2 Detailed Design Procedure

The TS3USB221E can be properly operated without any external components. However, TI recommends to connect any unused pins to ground through a 50-Ω resistor to prevent signal reflections back into the device.

7.2.3 Application Curves

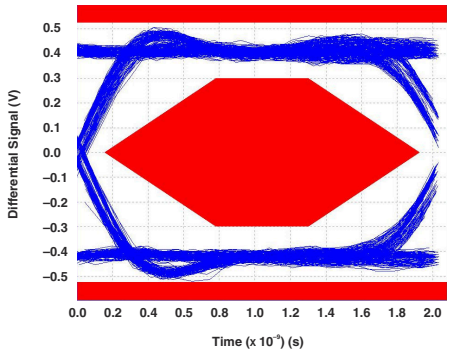


Figure 7-2. Eye Pattern: 480-Mbps USB Signal With No Switch (Through Path)

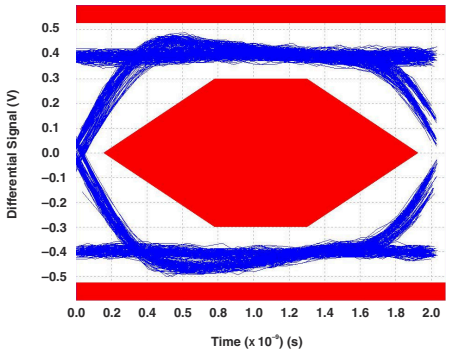


Figure 7-3. Eye Pattern: 480-Mbps USB Signal With Switch 1D Path

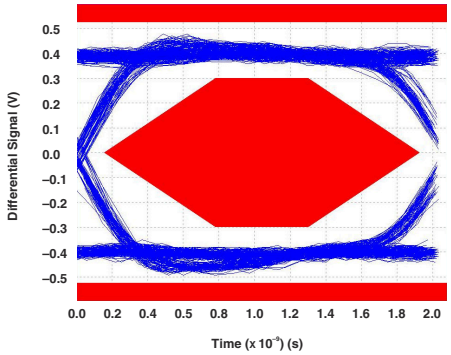


Figure 7-4. Eye Pattern: 480-Mbps USB Signal With Switch 2D Path

7.3 Power Supply Recommendations

Make sure that the power to the device supplied through the V_{CC} pin follows the USB 1.0, 1.1, and 2.0 standards. TI recommends placing a bypass capacitor as close as possible to the supply pin V_{CC} to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

7.4 Layout

7.4.1 Layout Guidelines

Place supply bypass capacitors as close to V_{CC} pin as possible and avoid placing the bypass caps near the D+/D– traces.

The high speed D+/D– traces should always be matched lengths and must be no more than 4 inches; otherwise, the eye diagram performance can be degraded. A high-speed USB connection is made through a shielded, twisted pair cable with a differential characteristic impedance. In layout, the impedance of D+ and D– traces should match the cable characteristic differential impedance for optimal performance.

Route the high-speed USB signals using a minimum of vias and corners to reduce signal reflections and impedance changes. When a via must be used, increase the clearance size around the via to minimize the capacitance. Each via introduces discontinuities in the transmission line of the signal and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points on twisted pair lines; through-hole pins are not recommended.

When it becomes necessary to turn 90°, use two 45° turns or an arc instead of making a single 90° turn. This reduces reflections on the signal traces by minimizing impedance discontinuities.

Do not route USB traces under or near crystals, oscillators, clock signal generators, switching regulators, mounting holes, magnetic devices or ICs that use or duplicate clock signals.

Avoid stubs on the high-speed USB signals because they cause signal reflections. If a stub is unavoidable, then the stub should be less than 200 mm.

Route all high-speed USB signal traces over continuous planes (V_{CC} or GND), with no interruptions.

Avoid crossing over anti-etch, commonly found with plane splits.

Due to high frequencies associated with the USB, a printed circuit board with at least four layers is recommended; two signal layers separated by a ground and power layer as shown in Figure 7-5.

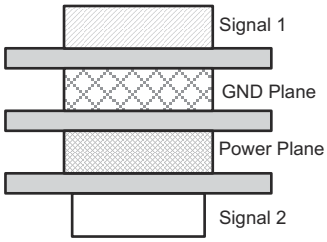


Figure 7-5. Four-Layer Board Stack-Up

The majority of signal traces should run on a single layer, preferably Signal 1. Immediately next to this layer should be the GND plane, which is solid with no cuts. Avoid running signal traces across a split in the ground or power plane. When running across split planes is unavoidable, sufficient decoupling must be used. Minimizing the number of signal vias reduces EMI by reducing inductance at high frequencies. For more information on layout guidelines, see *High Speed Layout Guidelines* and *USB 2.0 Board Design and Layout Guidelines*.

7.4.2 Layout Example

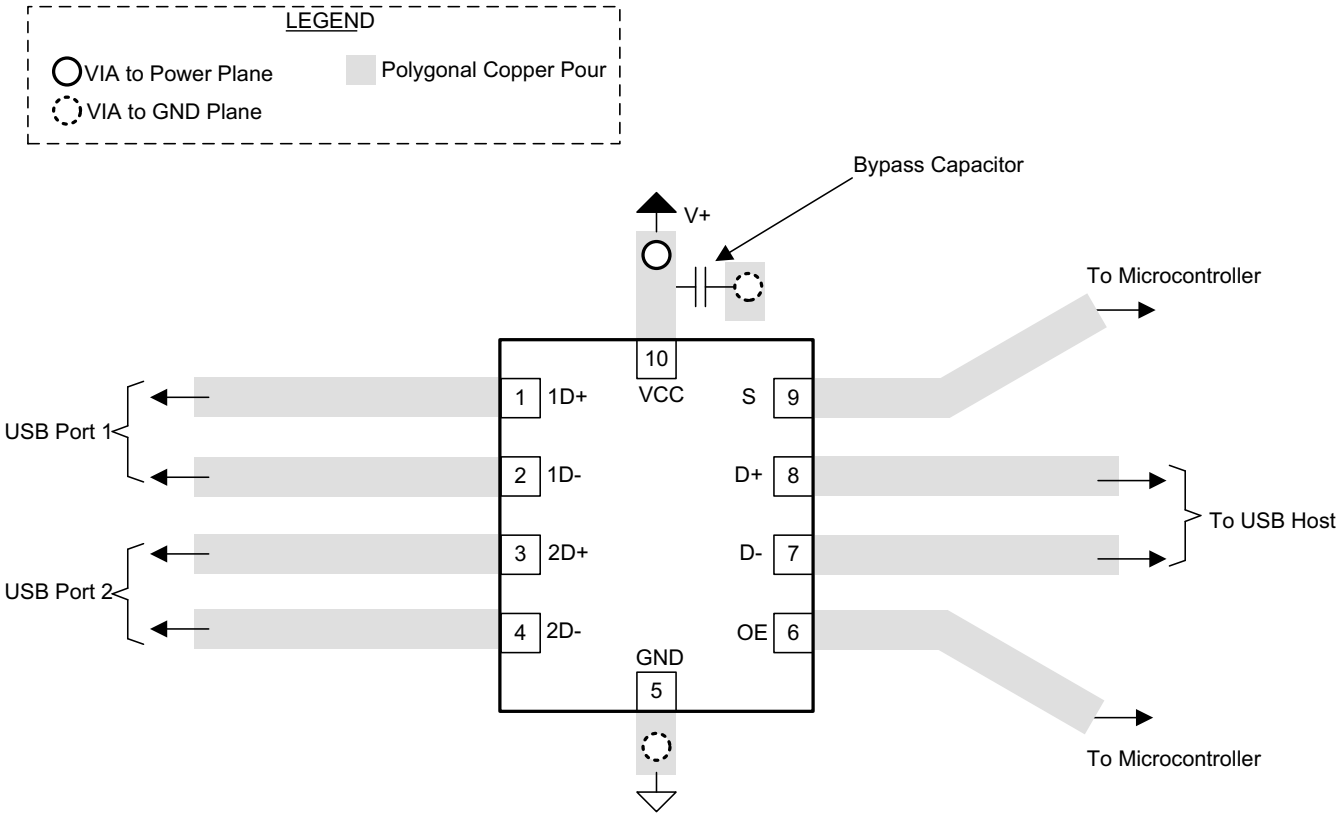


Figure 7-6. Package Layout Diagram

8 Device and Documentation Support

8.1 Documentation Support

8.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *Implications of Slow or Floating CMOS Inputs* application note
- Texas Instruments, *High Speed Layout Guidelines*
- Teas Instruments, *USB 2.0 Board Design and Layout Guidelines*

8.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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8.4 Trademarks

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8.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision D (September 2019) to Revision E (July 2024)	Page
• Updated the numbering format for tables, figures, and cross-references throughout the document	1
• Changed ESD HBM performance testing standard from: JESD 22 to: JEDEC JS-001	4
• Changed ESD CDM performance testing standard from: JESD22-C101 to: JEDEC JS-002	4
• Added tablenote to the Data input/output voltage parameter	4
• Changed RSE (UQFN) junction-to-ambient thermal resistance value from: 169.8°C/W to: 204.8°C/W	5
• Changed RSE (UQFN) junction-to-case (top) thermal resistance value from: 84.7°C/W to: 118.1°C/W	5
• Changed RSE (UQFN) junction-to-board thermal resistance value from: 94.9°C/W to: 121.5°C/W	5
• Changed RSE (UQFN) junction-to-top characterization parameter value from: 5.7°C/W to: 13.9°C/W	5
• Changed RSE (UQFN) junction-to-board characterization parameter value from: 94.9°C/W to: 121.2°C/W	5
• Changed the V_{IK} value in the *Electrical Characteristics* table from: –1.8V maximum to: –1.8V minimum	5
• Changed the graphs in the *Typical Characteristics* section	7

Changes from Revision C (April 2015) to Revision D (September 2019) **Page**

- Changed V_{CC} Operation FROM 2.5 V to 3.3 V TO 2.3 V to 3.6 V.....1

Changes from Revision B (July 2012) to Revision C (April 2015) **Page**

- Added *Pin Configuration and Functions* section, *ESD Ratings* table, *Thermal Information* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section 1
- Removed *Ordering Information* table..... 1

Changes from Revision A (February 2010) to Revision B (July 2012) **Page**

- Updated TOP-SIDE MARKING for RSE package in *Ordering Information* table..... 1

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS3USB221EDRCR	ACTIVE	VSON	DRC	10	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZVM	Samples
TS3USB221ERSER	ACTIVE	UQFN	RSE	10	3000	RoHS & Green	NIPDAU | NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(LGH, LGO, LGR, LGV)	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

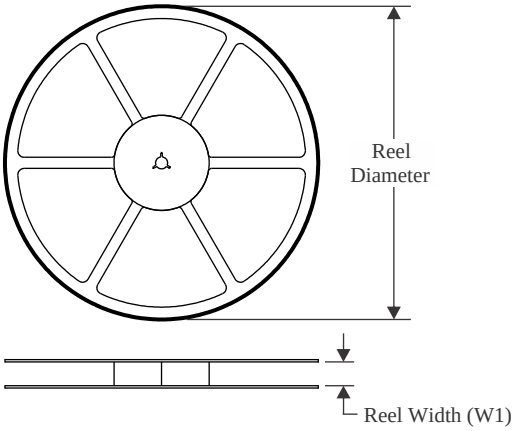
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

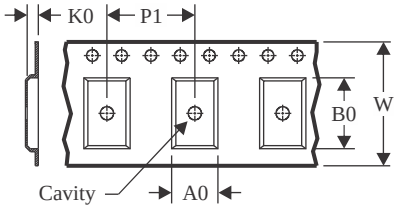
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

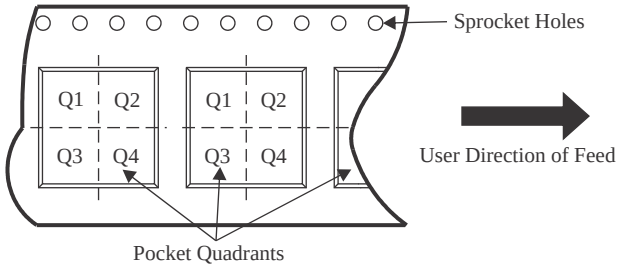


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

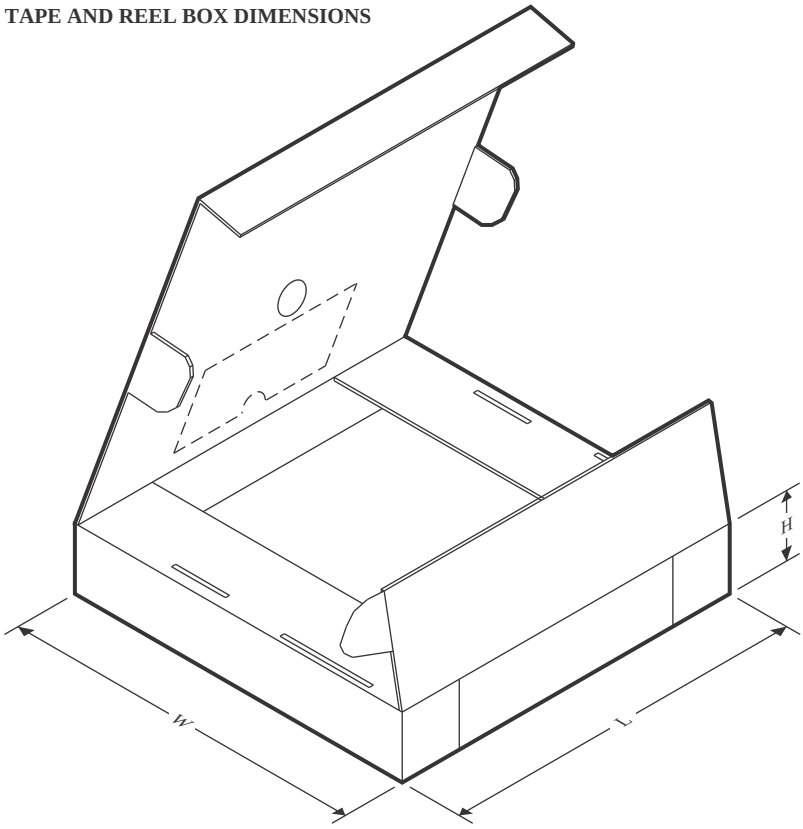
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3USB221EDRCR	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TS3USB221ERSER	UQFN	RSE	10	3000	180.0	9.5	1.7	2.2	0.75	4.0	8.0	Q1
TS3USB221ERSER	UQFN	RSE	10	3000	180.0	8.4	1.68	2.13	0.76	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

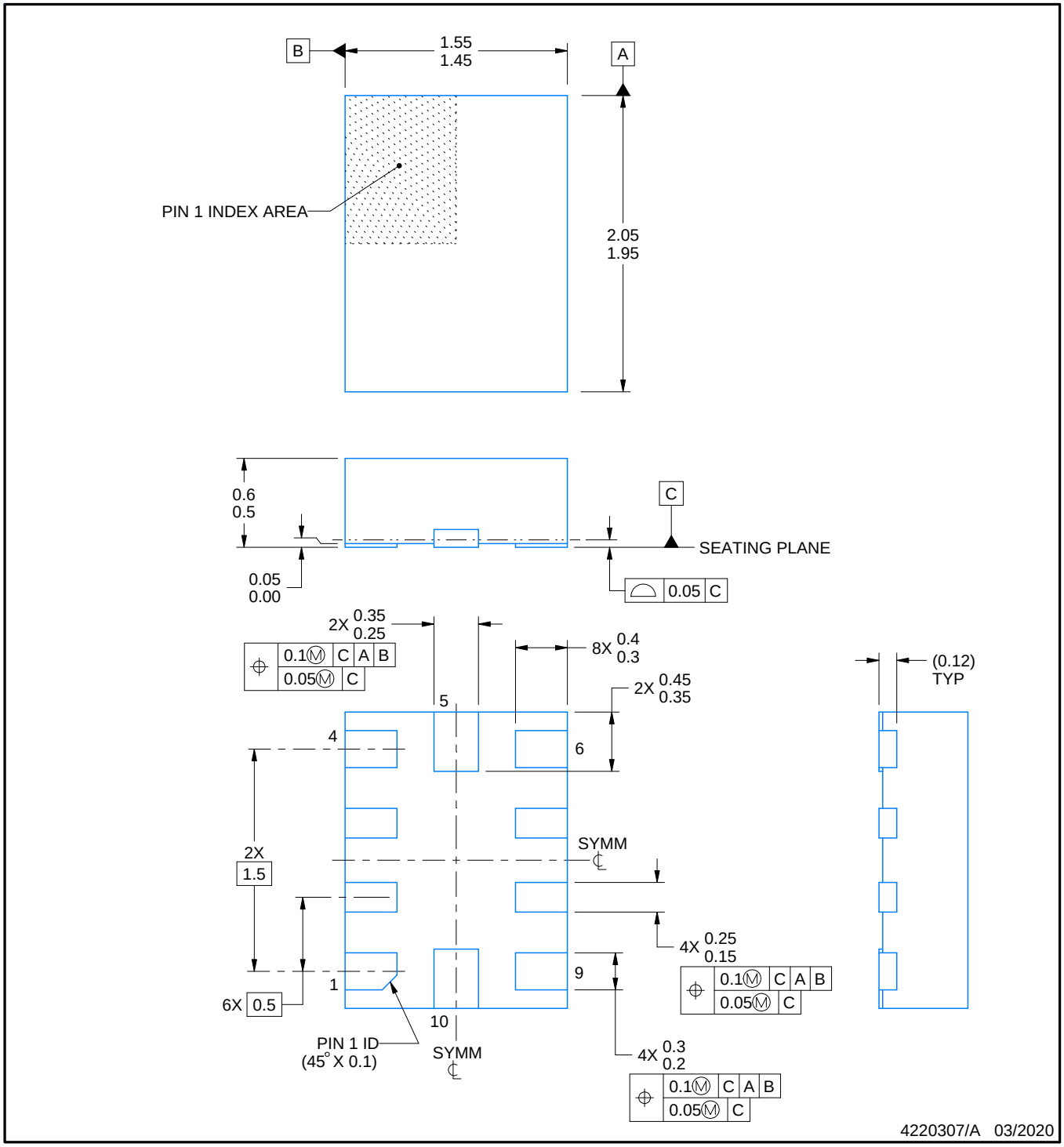
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3USB221EDRCR	VSON	DRC	10	3000	356.0	356.0	35.0
TS3USB221ERSER	UQFN	RSE	10	3000	189.0	185.0	36.0
TS3USB221ERSER	UQFN	RSE	10	3000	202.0	201.0	28.0

RSE0010A

PACKAGE OUTLINE

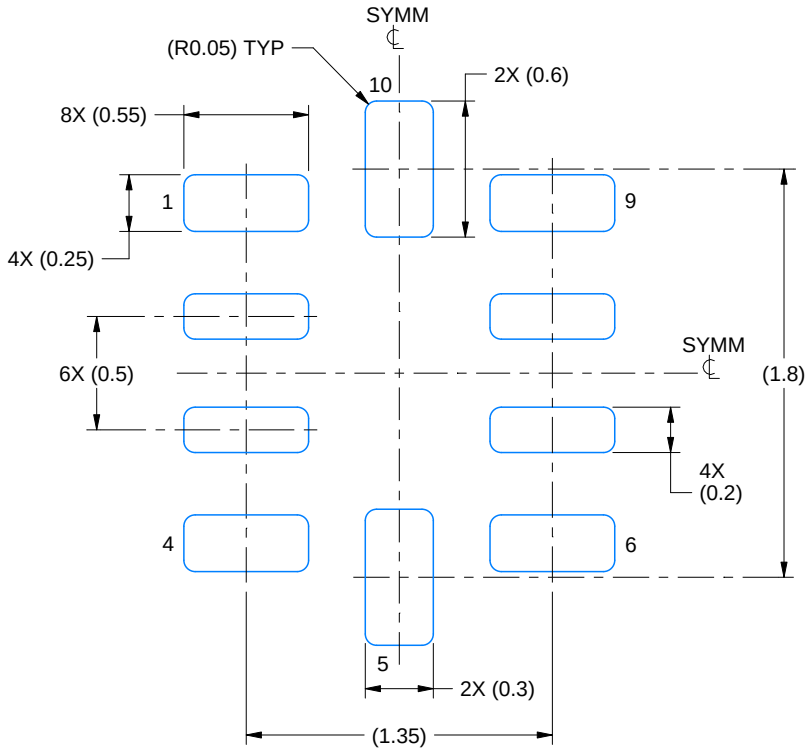
UQFN - 0.6 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

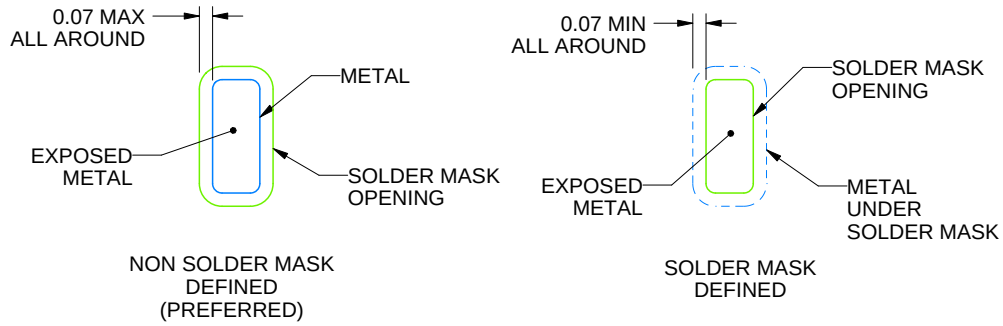


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:30X

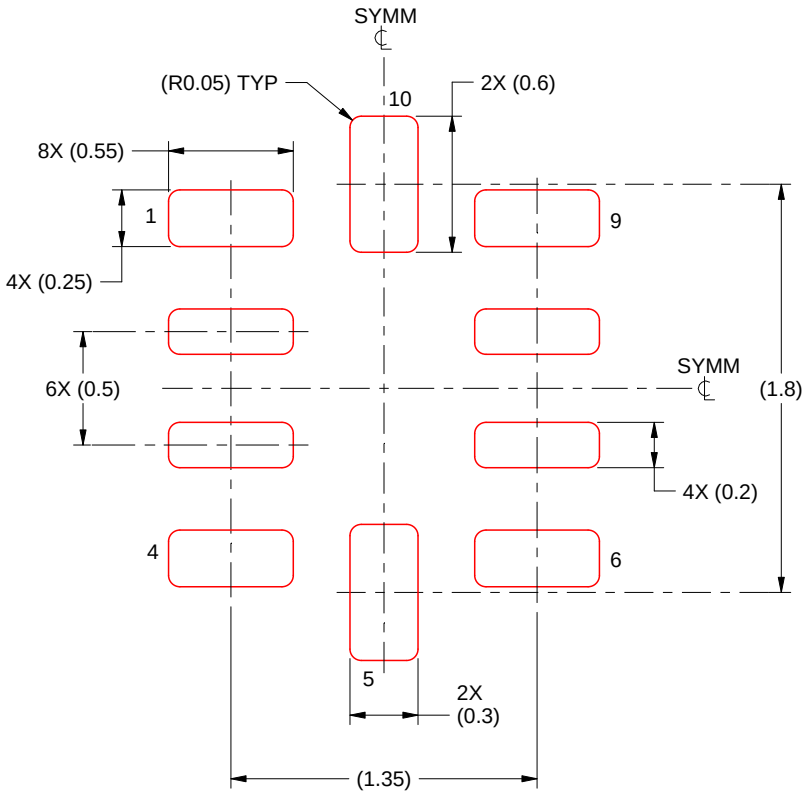


SOLDER MASK DETAILS
NOT TO SCALE

4220307/A 03/2020

NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICKNESS
SCALE: 30X

4220307/A 03/2020

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

GENERIC PACKAGE VIEW

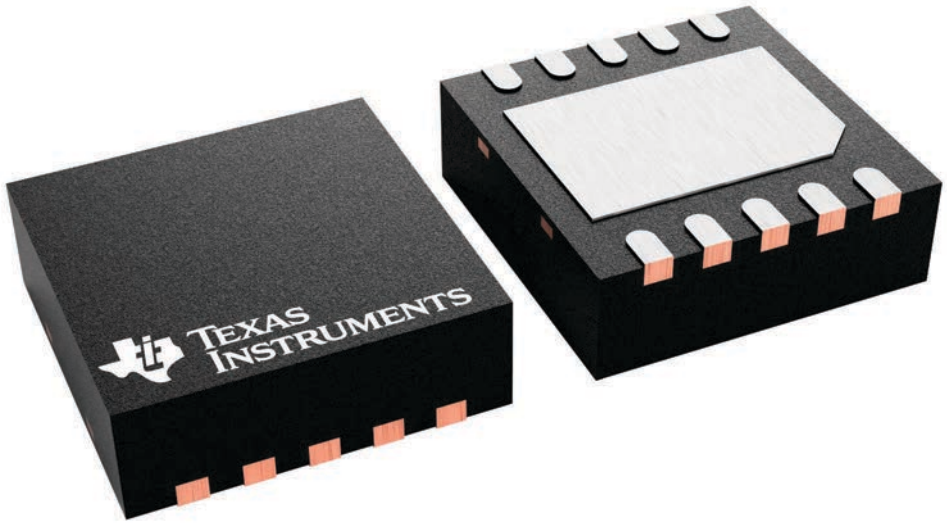
DRC 10

VSON - 1 mm max height

3 x 3, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



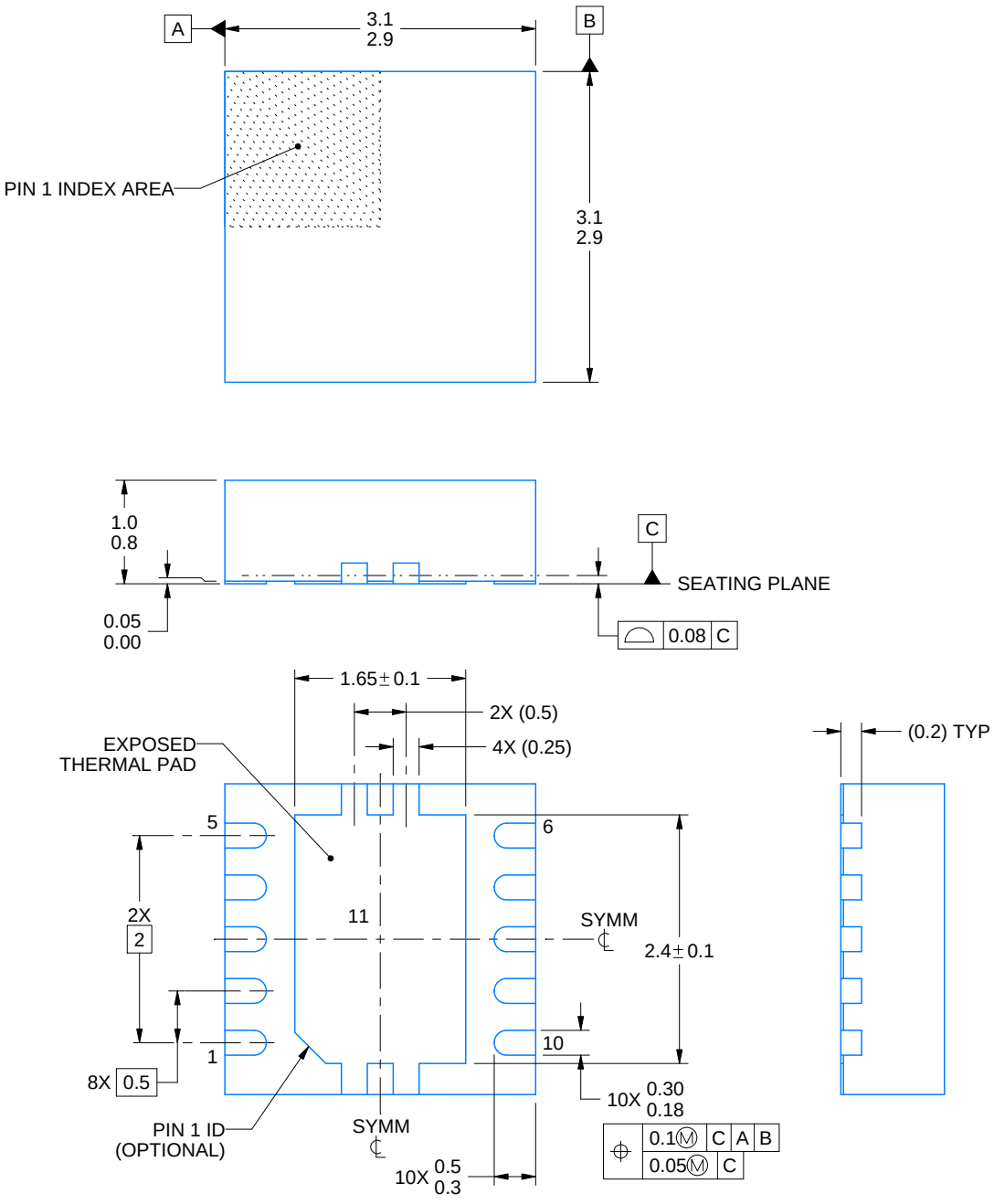
4226193/A

DRC0010J

PACKAGE OUTLINE

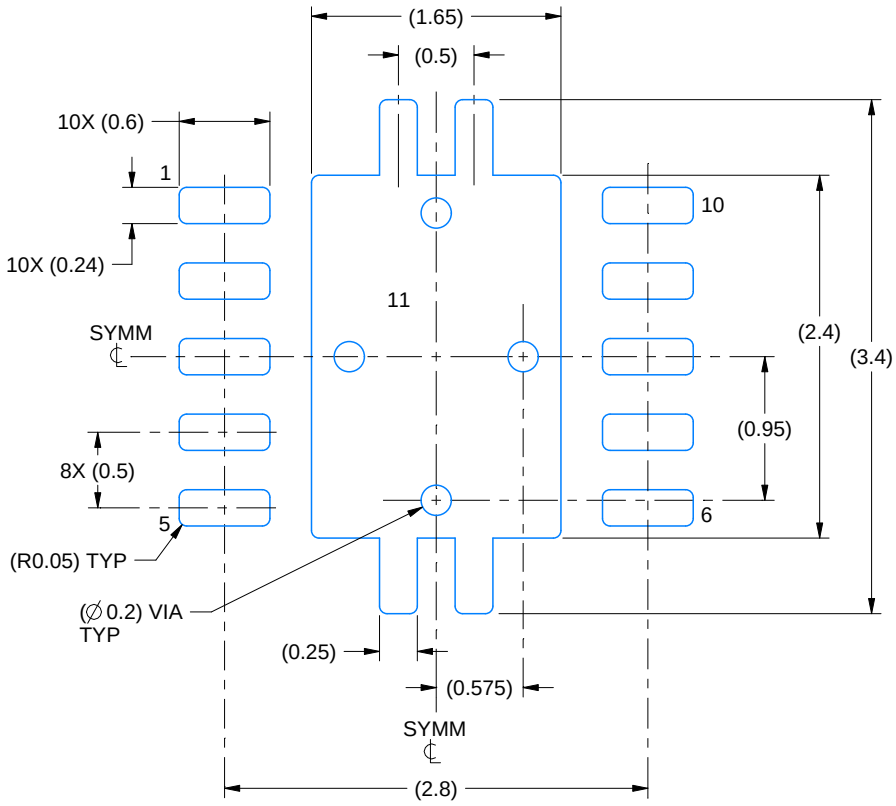
VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

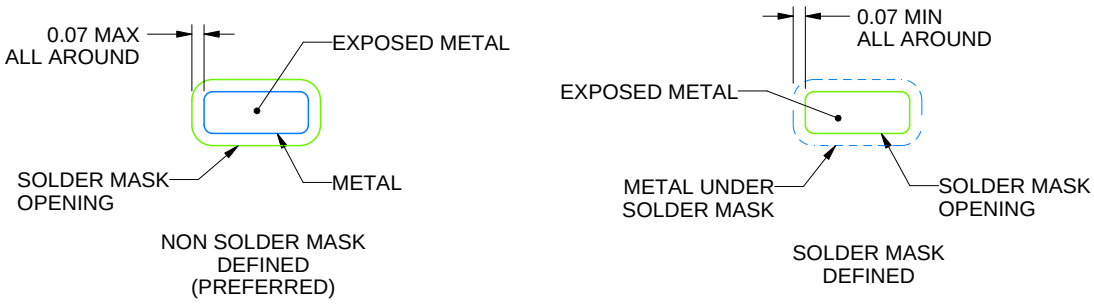


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X



SOLDER MASK DETAILS

4218878/B 07/2018

NOTES: (continued)

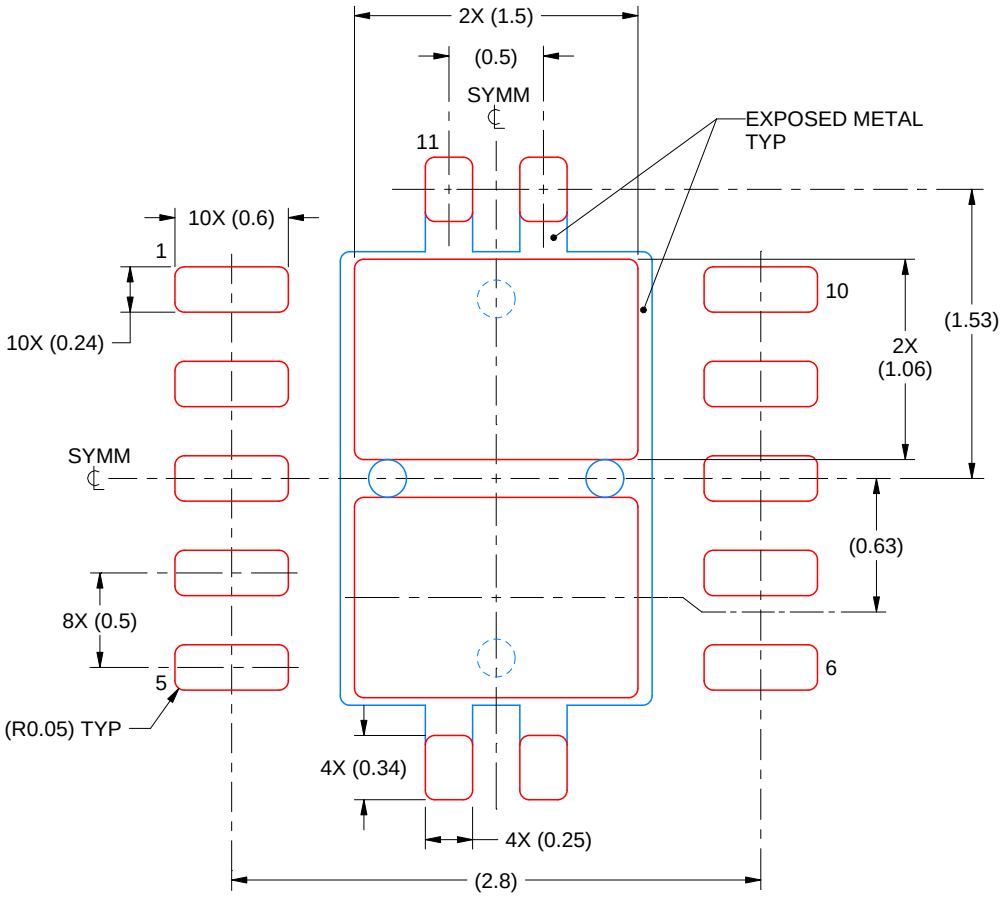
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

DRC0010J

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 11:
80% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

4218878/B 07/2018

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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